

In the Abstract:

Please delete the Abstract and substitute the following Abstract therefor:

A vertical field effect transistor includes a microelectronic substrate having a trench, the trench defining a sidewall. A conformal monocrystalline silicon layer is provided on the sidewall, including a drain region adjacent the substrate, a source region remote from the substrate, and a channel region between the source and drain regions. A plug is provided in the trench. A gate insulating layer is provided adjacent the channel and a gate electrode is provided on the gate insulating layer.